PROCESS **CP275**

Central™ Semiconductor Corp.

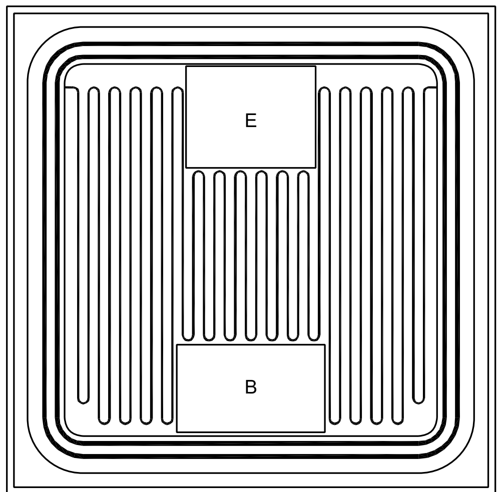
Power Transistor

4.0 Amp NPN Silicon Power Transistor Chip

PROCESS DETAILS

Die Size	105 x 105 MILS
Die Thickness	8.5 MILS
Base Bonding Pad Area	32 x 19 MILS
Emitter Bonding Pad Area	28 x 22 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Ti/Ni/Ag - (300Å, 1,000Å, 10,000Å)

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

980

PRINCIPAL DEVICE TYPES

MJE13005

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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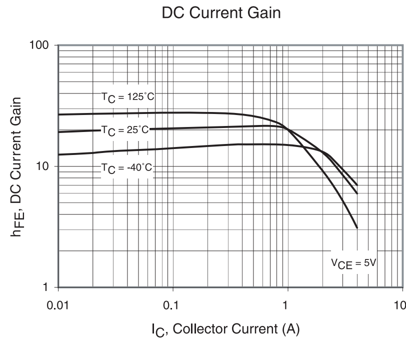
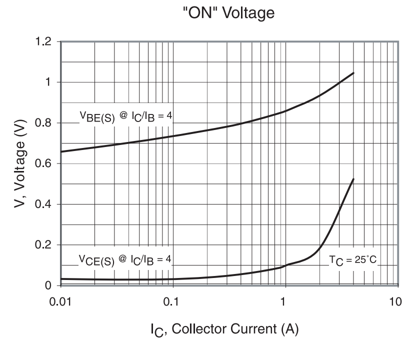
Central™
Semiconductor Corp.

PROCESS CP275
Typical Electrical Characteristics

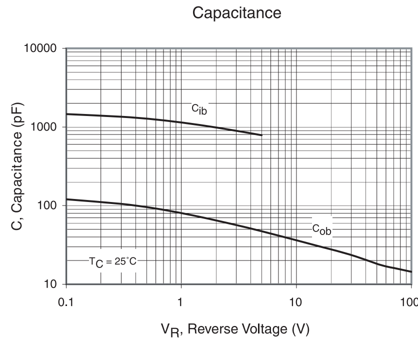
DC Current Gain



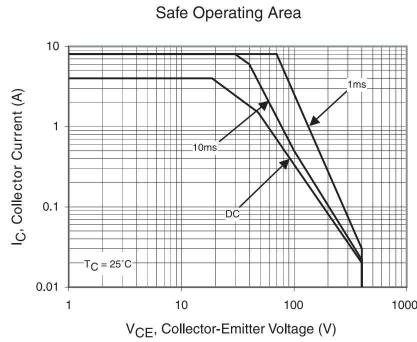
"ON" Voltage



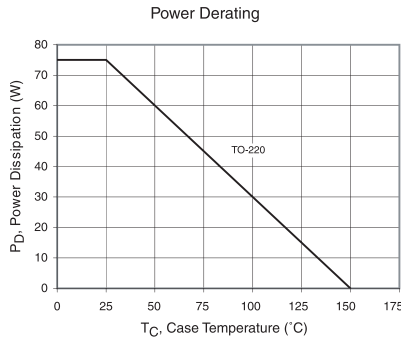
Capacitance



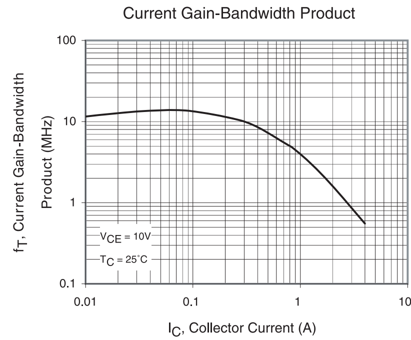
Safe Operating Area



Power Derating



Current Gain-Bandwidth Product



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